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(54) **Title:** METHOD AND APPARATUS FOR REMOVING PARTICLES OR PHOTORESIST ON SUBSTRATES

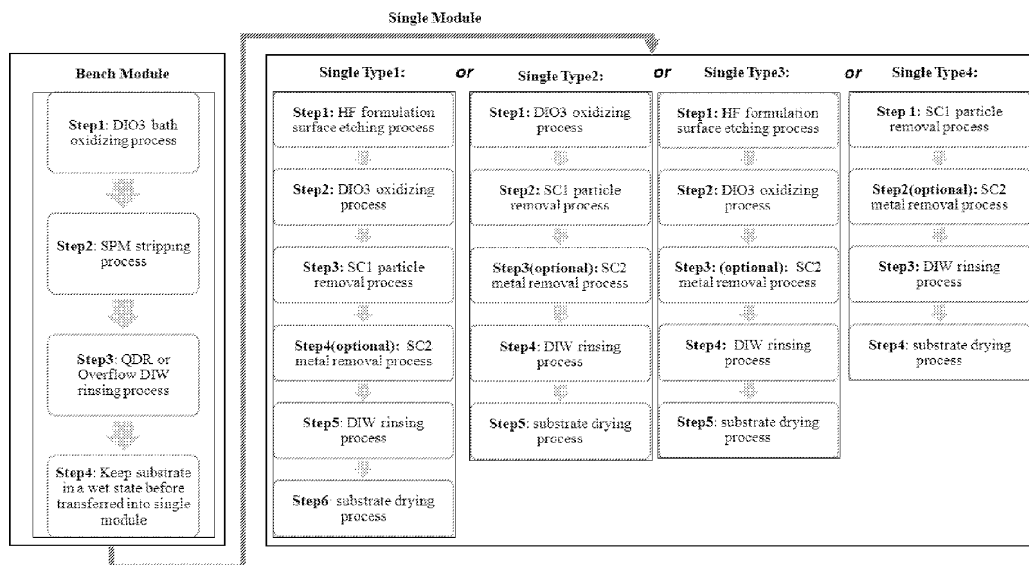


FIG 2

(57) **Abstract:** Methods and an apparatus for removing particles or photoresist on substrates. In an embodiment, a method comprises the following steps: transferring one or more substrates into a DIO₃ solution accommodated in a DIO₃ bath; after the one or more substrates are processed in the DIO₃ bath, taking the one or more substrates out from the DIO₃ bath and transferring the one or more substrates into a SPM solution accommodated in a SPM bath; after the one or more substrates are processed in the SPM bath, taking the one or more substrates out from the SPM bath and rinsing the one or more substrates; and transferring the one or more substrates to one or more single chambers to perform single substrate cleaning and drying process. The method combines DIO₃ and SPM in one cleaning sequence, which can remove particles or photoresist, especially remove photoresist treated by medium dose or high dose of ion implantation.

[Continued on next page]

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